

**Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

**Product Summary**



$V_{DS}$	-60	V
$I_D$	-1.5	A
$R_{DS(ON)}$ (at $V_{GS}=-10V$ )	120	m $\Omega$
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$ )	165	m $\Omega$

**Applications**

- High Frequency Point-of-Load, Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch



**Absolute Maximum Ratings( $T_C=25^{\circ}C$ , unless otherwise noted)**

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	-60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>1</sup>	$I_D@T_C=25^{\circ}C$	-1.5	A
Continuous Drain Current <sup>1</sup>	$I_D@T_C=100^{\circ}C$	-0.95	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	-4.5	A
Total Power Dissipation	$P_D$	1.5	W
Storage Temperature Range	$T_{STG}$	-55 to 150	$^{\circ}C$
Operating Junction Temperature Range	$T_J$	-55 to 150	$^{\circ}C$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient <sup>1</sup>	$R_{\theta JA}$	---	250	$^{\circ}C/W$
Thermal Resistance Junction-Case <sup>1</sup>	$R_{\theta JC}$	---	80	$^{\circ}C/W$

**Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-60	---	---	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-1.5A	---	100	120	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1A	---	130	165	mΩ
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.2	---	-2.5	V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V	---	---	-1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-25V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-1A	---	12	---	nC
Gate-Source Charge	Q <sub>gs</sub>		---	1.5	---	
Gate-Drain Charge	Q <sub>gd</sub>		---	2.5	---	
Turn-On Delay Time	T <sub>d(on)</sub>	V <sub>DD</sub> =-25V, V <sub>GS</sub> =-4.5V, R <sub>G</sub> =3Ω, I <sub>D</sub> =-1A	---	10	---	ns
Rise Time	T <sub>r</sub>		---	11	---	
Turn-Off Delay Time	T <sub>d(off)</sub>		---	50	---	
Fall Time	T <sub>f</sub>		---	28	---	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-25V, V <sub>GS</sub> =0V, f=1MHz	---	620	---	pF
Output Capacitance	C <sub>oss</sub>		---	110	---	
Reverse Transfer Capacitance	C <sub>rss</sub>		---	65	---	

**Drain-Source Diode Characteristics**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode Forward Voltage <sup>2</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1.5A, T <sub>J</sub> =25°C	---	---	-1.2	V

**Note:**

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature

**Typical Characteristics**

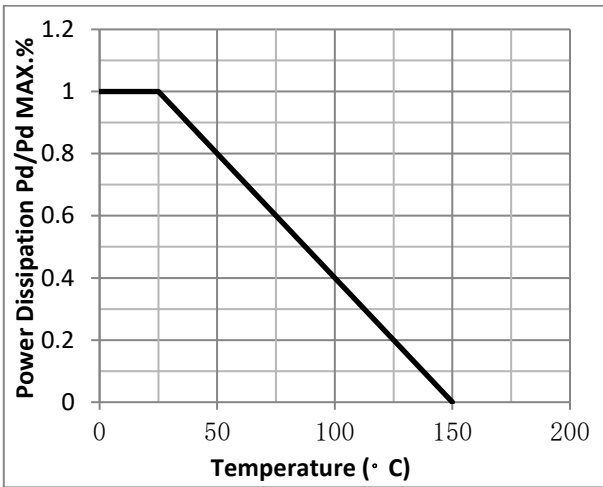


Fig.1 Power Dissipation Derating Curve

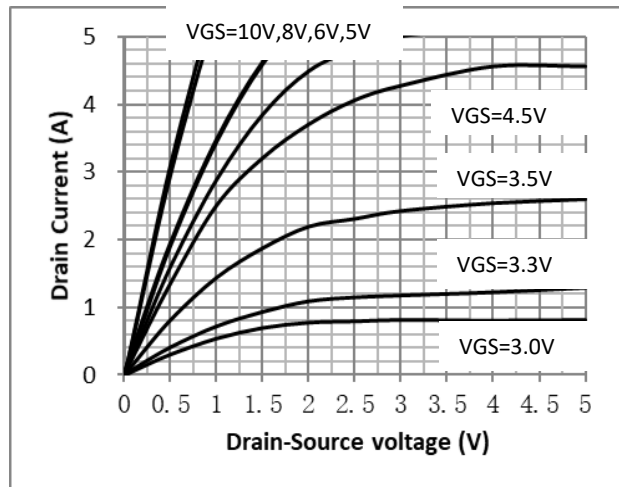


Fig.2 Typical output Characteristics

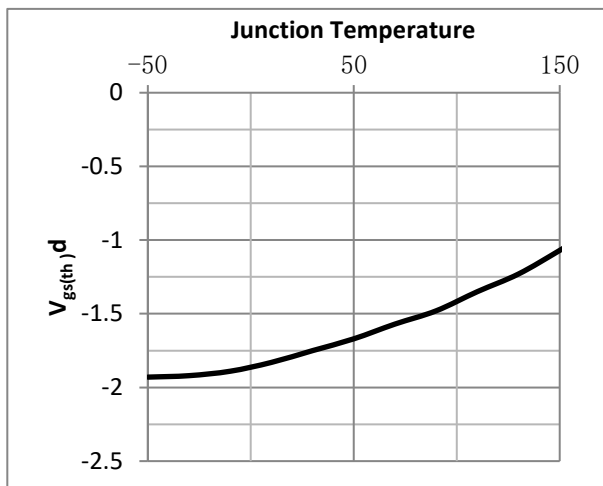


Fig.3 Threshold Voltage V.S Junction Temperature

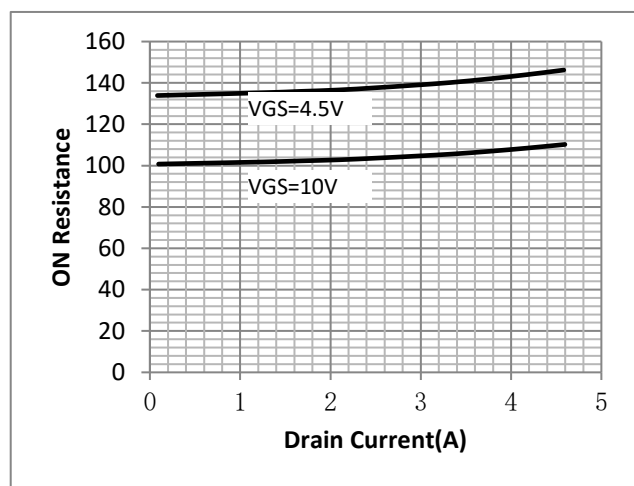


Fig.4 Resistance V.S Drain Current

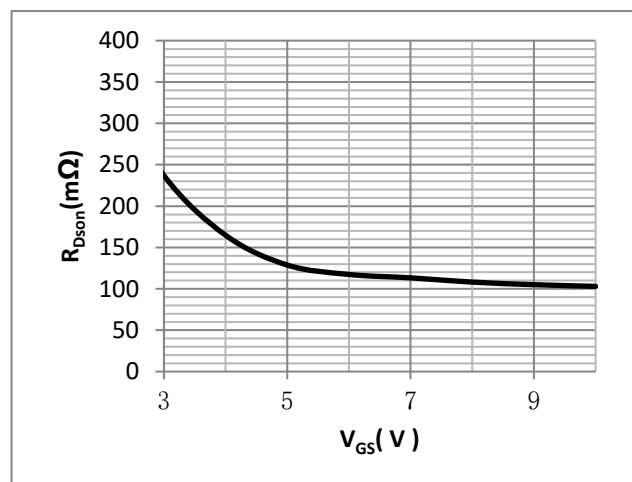


Fig.5 On-Resistance VS Gate Source Voltage

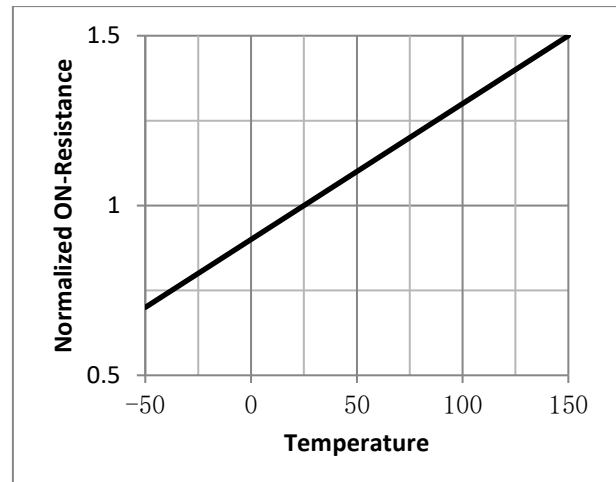


Fig.6 On-Resistance V.S Junction Temperature

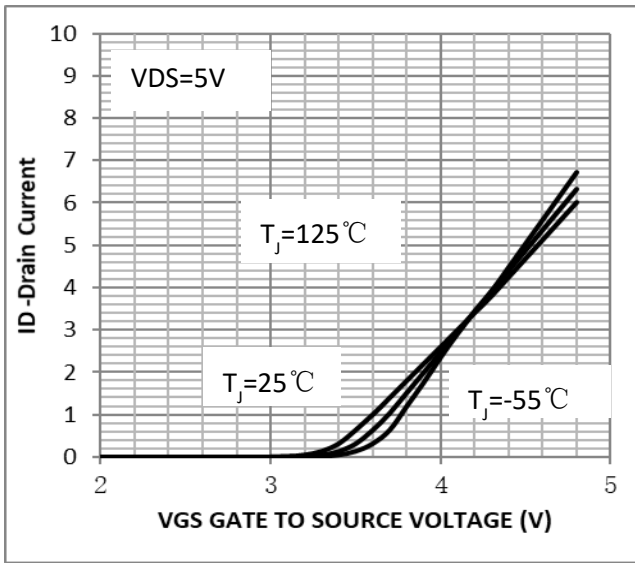
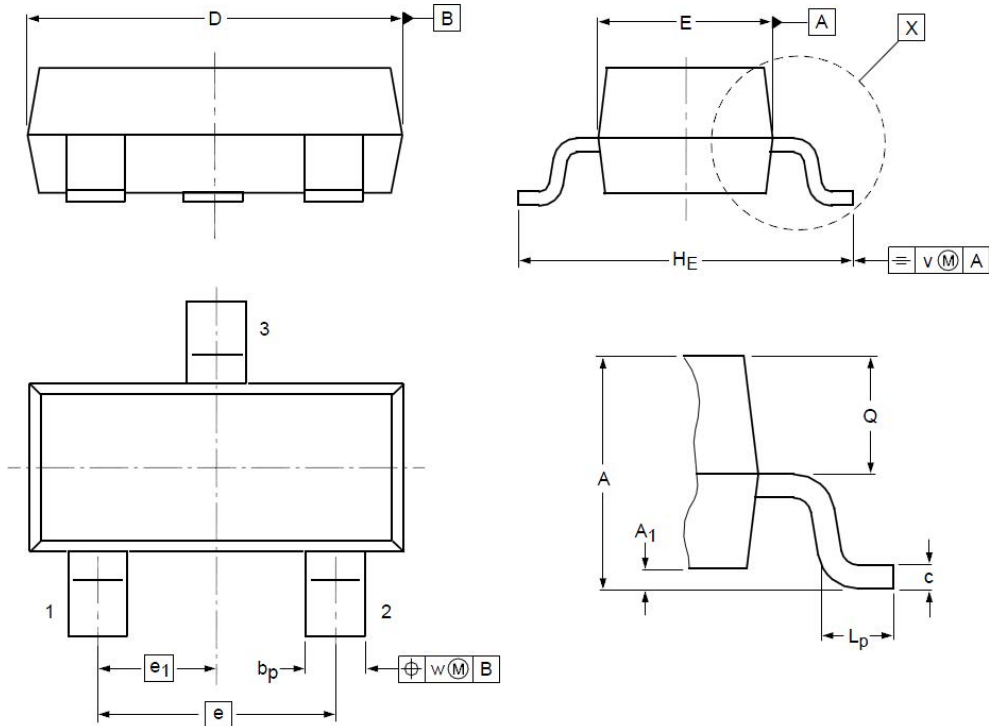


Fig.7 Transfer Characteristics

**SOT23 Package Outline Dimensions**



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
<b>A</b>	0.90	1.05	1.20	<b>e<sub>1</sub></b>	--	0.95	--
<b>A<sub>1</sub></b>	0.01	0.05	0.10	<b>H<sub>E</sub></b>	2.10	2.40	2.50
<b>b<sub>p</sub></b>	0.38	0.42	0.48	<b>L<sub>p</sub></b>	0.40	0.50	0.60
<b>c</b>	0.09	0.13	0.15	<b>Q</b>	0.45	0.49	0.55
<b>D</b>	2.80	2.92	3.00	<b>V</b>	--	0.20	--
<b>E</b>	1.20	1.33	1.40	<b>W</b>	--	0.10	--
<b>e</b>	--	1.90	--				